



Docket No.: 49657-801

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of

Tomohide TERASHIMA

Serial No.: 09/661,035

Filed: September 13, 2000

For: SEMICONDUCTOR DEVICE

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Group Art Unit: 2811

Examiner: LOKE, Steven Ho Yin

PATENT

#7/a  
6/24/02  
Sunder

**AMENDMENT**

Commissioner for Patents  
Washington, DC 20231

Sir:

The Following Amendments and Remarks are submitted in response to the Office  
Action dated March 13, 2002.

**IN THE SPECIFICATION:**

Please delete the title and insert the following new title:

-- SEMICONDUCTOR DEVICE WITH REGION THAT CHANGES DEPTH  
ACROSS THE DIRECTION OF CURRENT FLOW --.

Please replace the paragraph beginning at page 10, line 19, with the following  
rewritten paragraph:

+ Assuming that N<sup>-</sup>-type epitaxial layer 2 has an impurity concentration of N<sub>A</sub>, P-  
type diffusion region 7 has an impurity concentration of N<sub>D</sub>, neighboring P-type diffusion  
regions 7 are spaced by a distance of W, a required breakdown voltage is V, an amount of

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